Device Modeling Report

COMPONENTS: Power MOSFET (Professional)
PART NUMBER: TPC6105
MANUFACTURER: TOSHIBA
Body Diode (Professional) / ESD Protection Diode

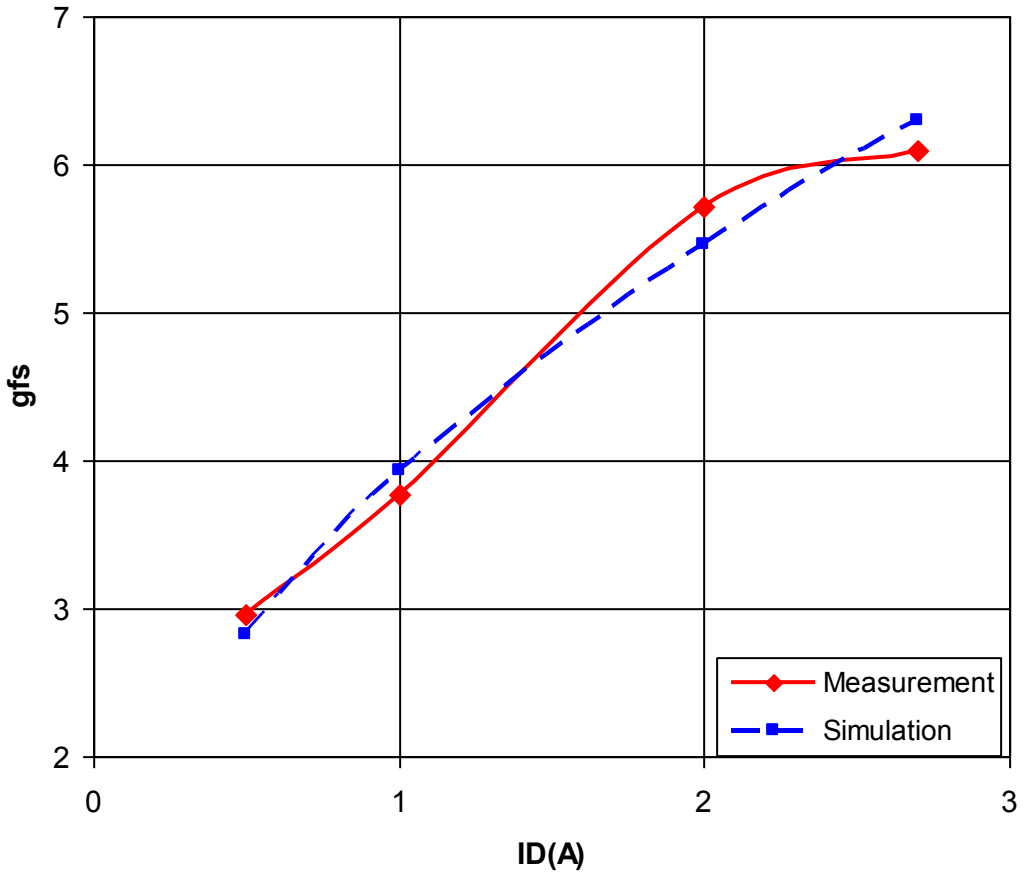
Bee Technologies Inc.

MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

Transconductance Characteristic

Circuit Simulation Result

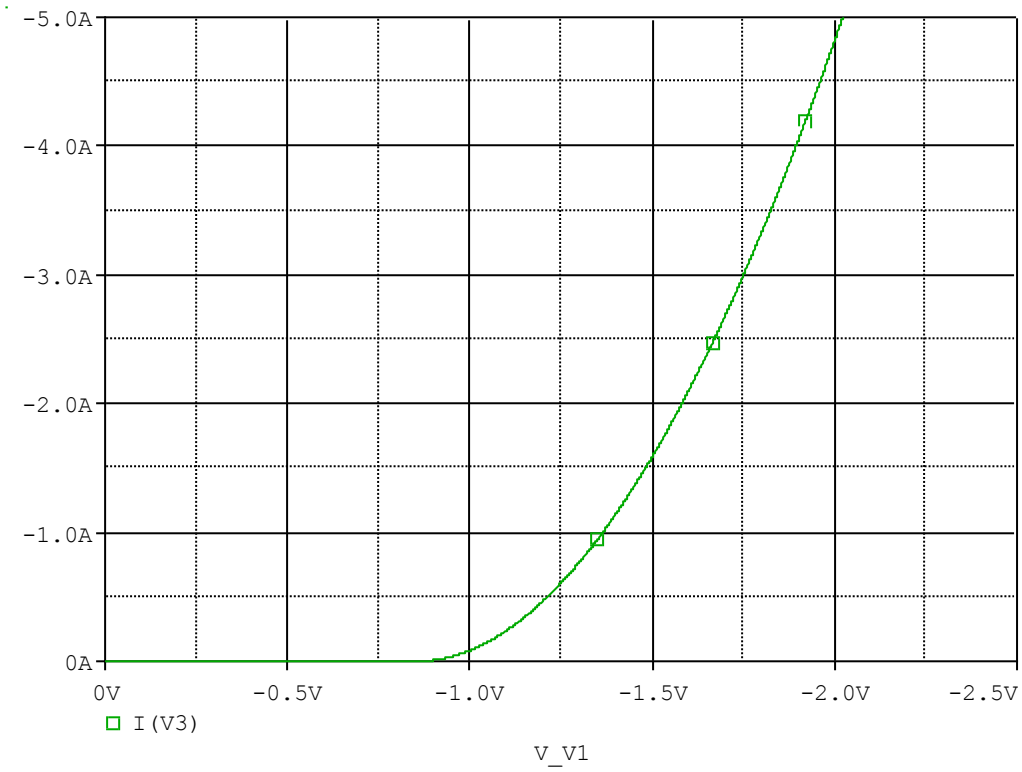


Comparison table

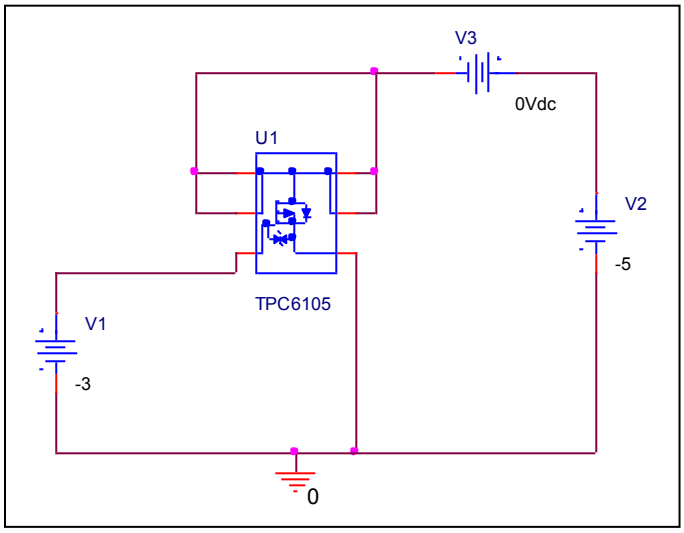
- Id(mA)	gfs		Error(%)
	Measurement	Simulation	
0.5	2.959	2.825	-4.529
1	3.774	3.937	4.319
2	5.714	5.464	-4.375
2.7	6.000	6.294	4.900

Vgs-Id Characteristic

Circuit Simulation result

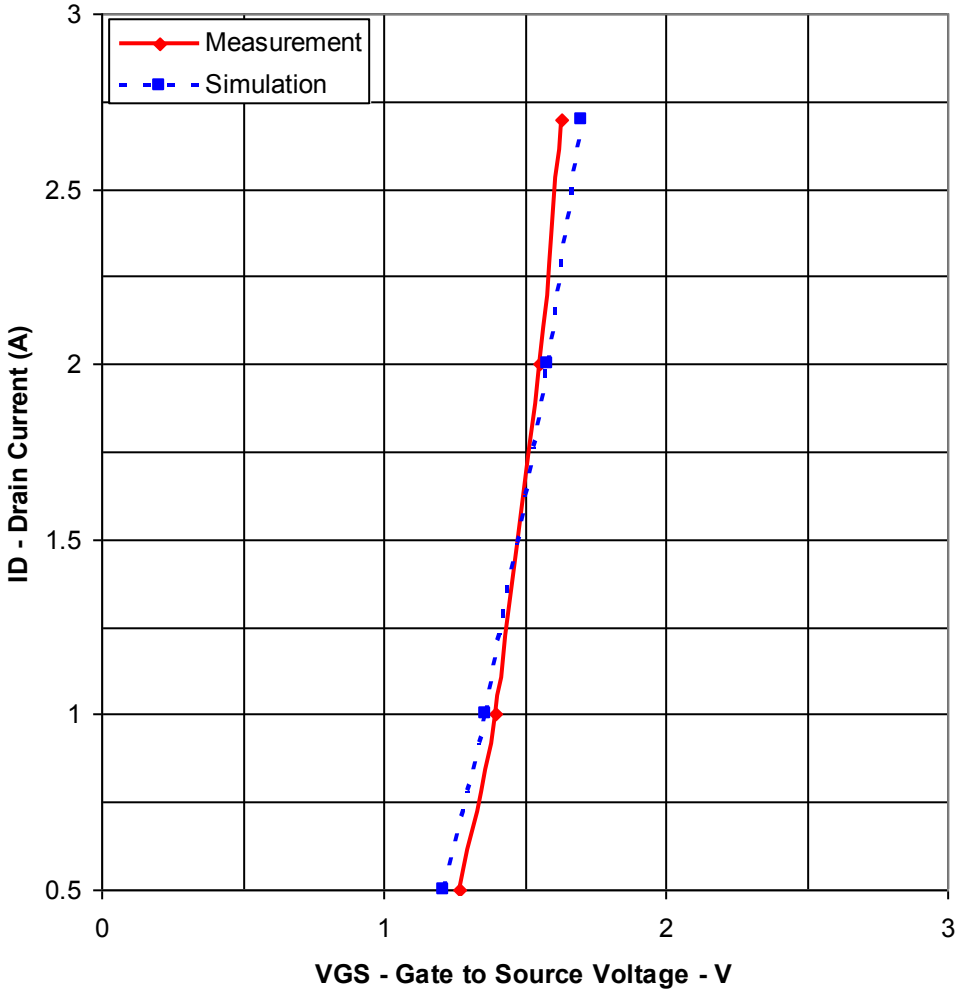


Evaluation circuit



Comparison Graph

Circuit Simulation Result

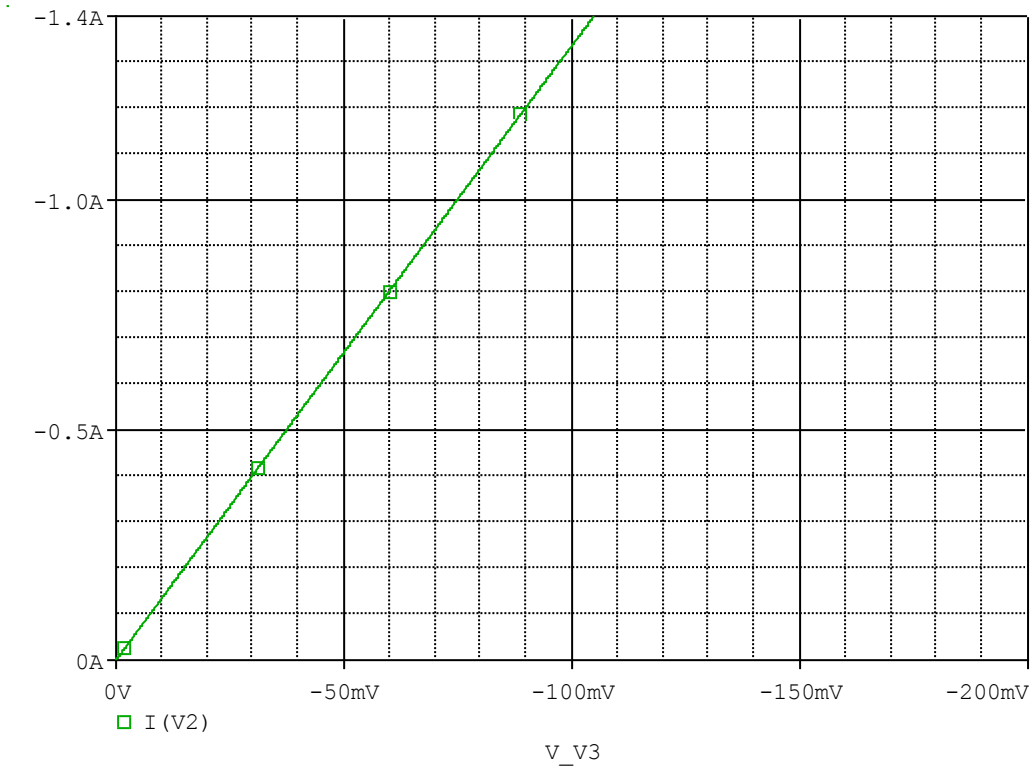


Simulation Result

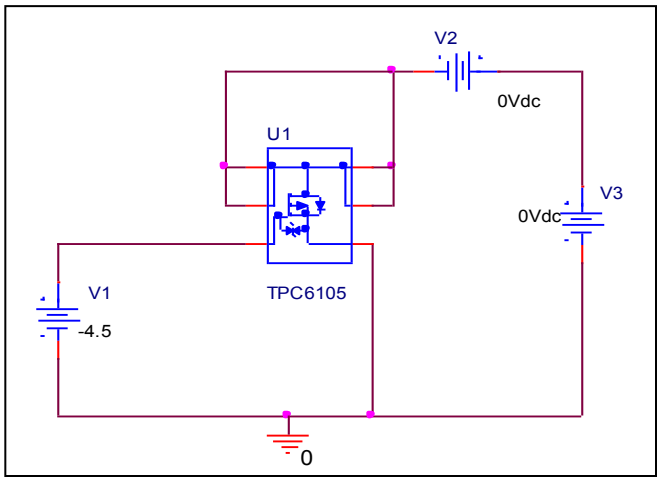
- I_D(mA)	- V_{GS}(V)		Error (%)
	Measurement	Simulation	
0.5	1.27	1.2126	-4.520
1	1.4	1.3640	-2.571
2	1.55	1.5811	2.006
2.7	1.63	1.7026	4.454

Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit

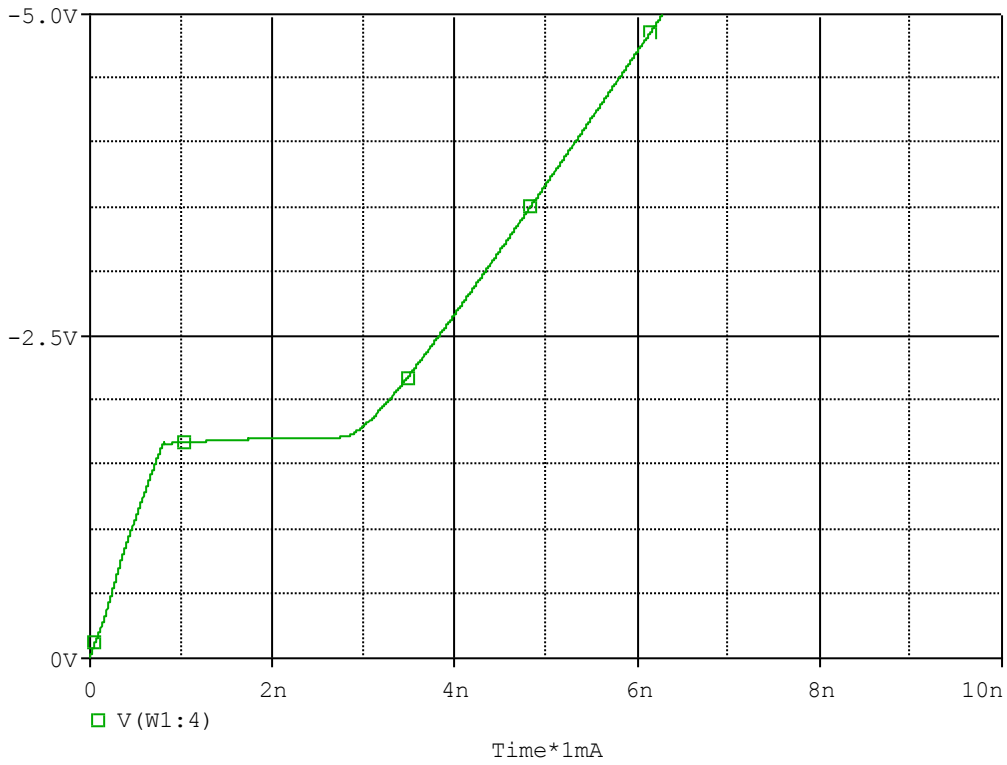


Simulation Result

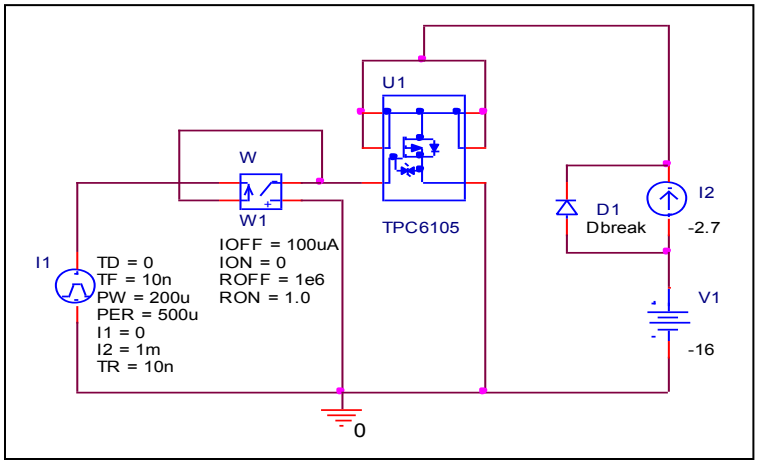
I_D=-1.4A, V_{GS}=-4.5V	Measurement		Simulation		Error (%)
R_{DS} (on)	72.000	mΩ	74.844	mΩ	3.950

Gate Charge Characteristic

Circuit Simulation result



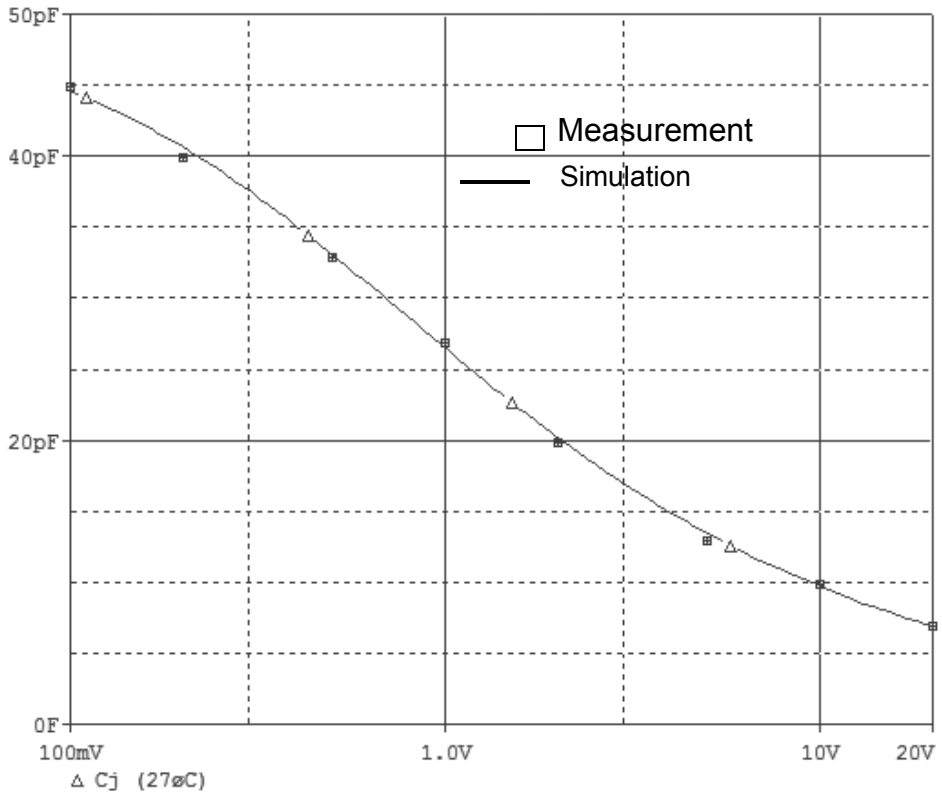
Evaluation circuit



Simulation Result

V_{DD}=-16V,I_D=-2.7A ,V_{GS}=-5V	Measurement	Simulation	Error (%)
Qgs(nC)	0.8	0.809	1.125
Qgd(nC)	2	1.971	-1.450
Qg(nC)	6.2	6.281	1.306

Capacitance Characteristic

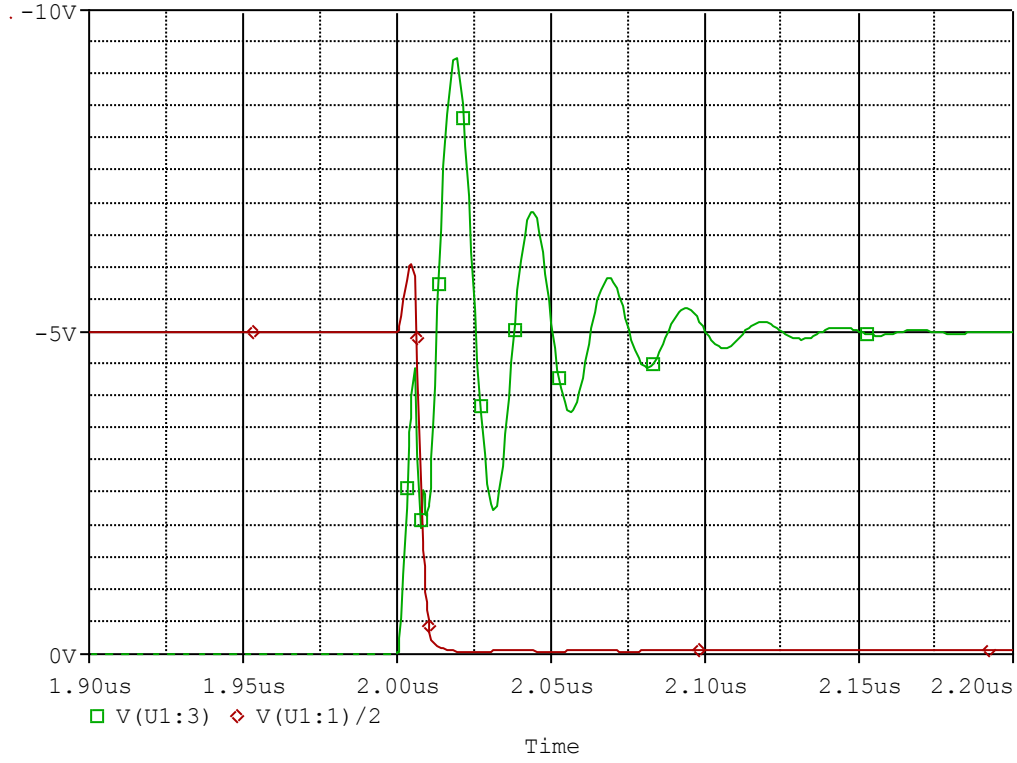


Simulation Result

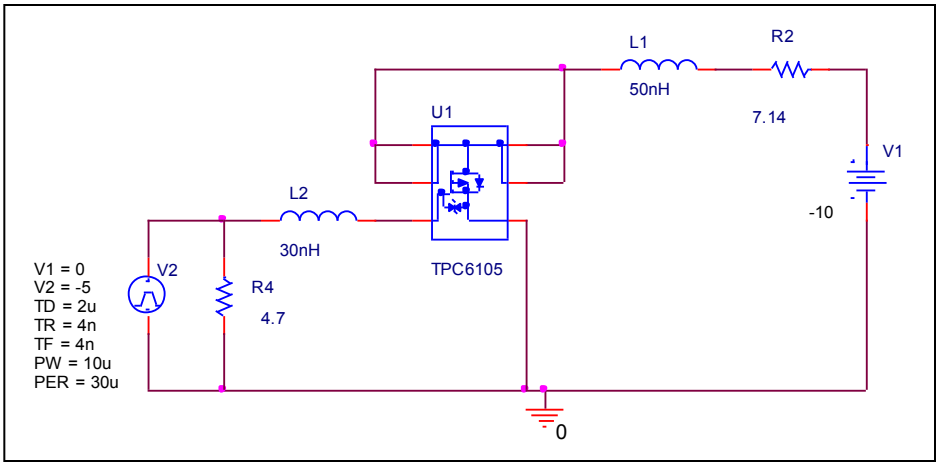
- V_{DS}(V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
0.1	45	44.5	-1.111
0.2	40	40.6	1.500
0.5	33	33.1	0.303
1	27	26.5	-1.852
2	20	20.2	1.000
5	13	13.4	3.077
10	10	9.7	-3.000
20	7	6.9	-1.429

Switching Time Characteristic

Circuit Simulation result



Evaluation circuit

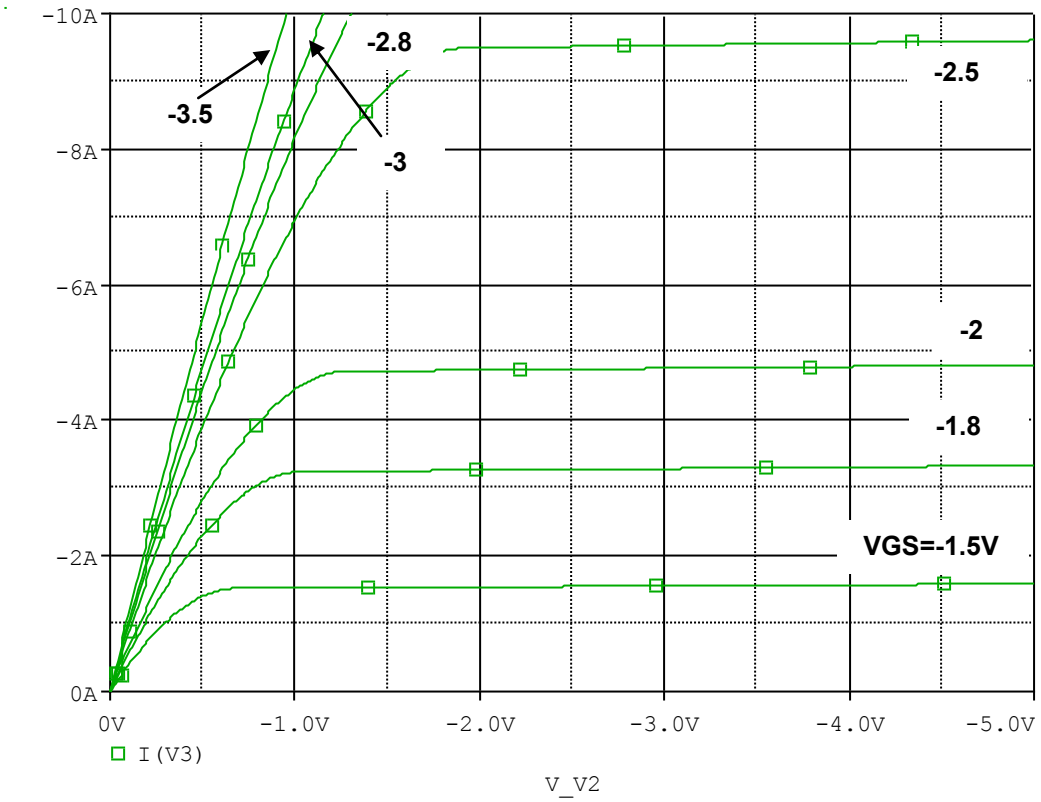


Simulation Result

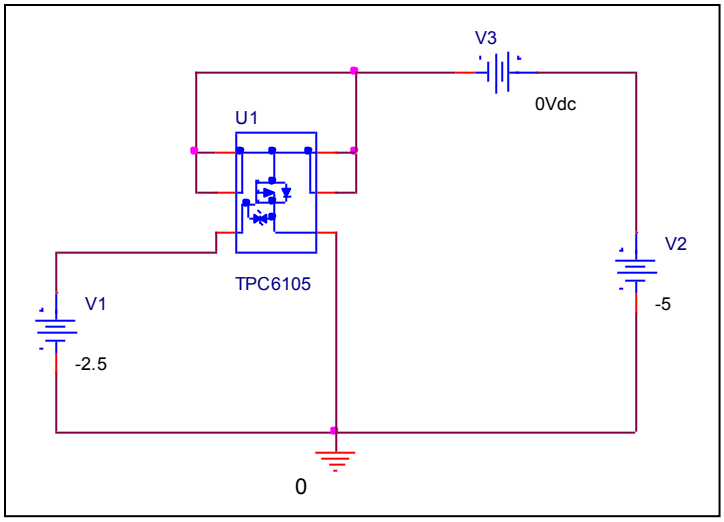
I_D=-1.4 A, V_{DD}=-10V V_{GS}=0/-5V	Measurement	Simulation	Error(%)
Ton(ns)	9.000	9.0494	0.549

Output Characteristic

Circuit Simulation result

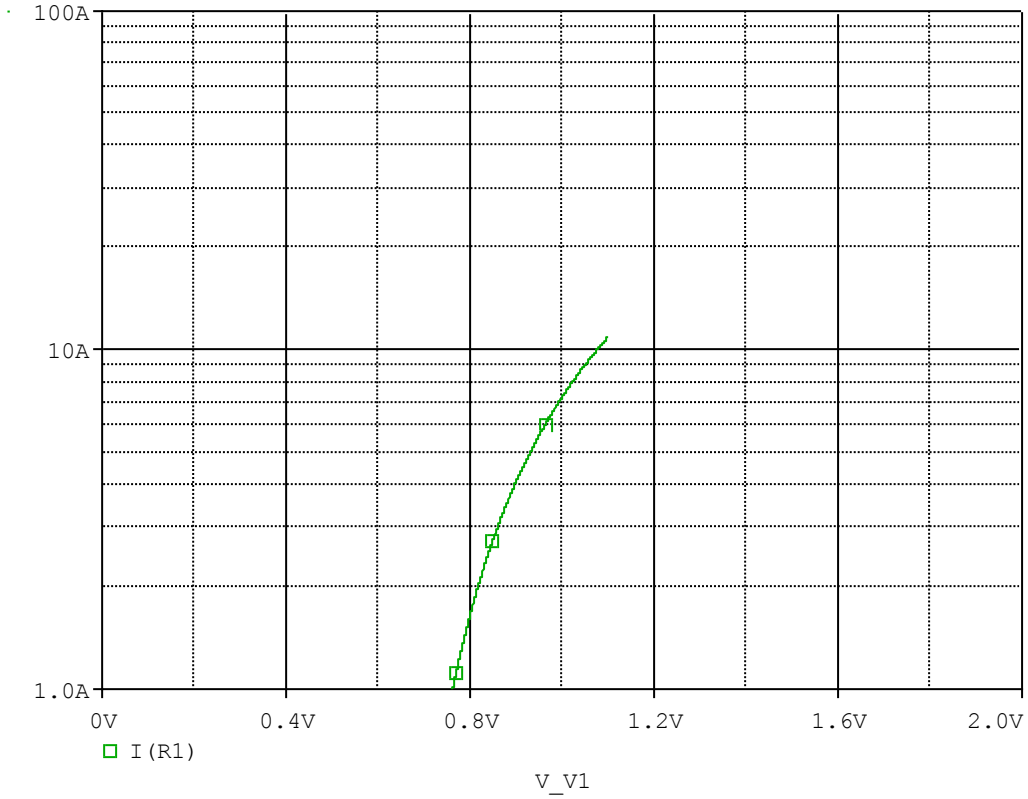


Evaluation circuit

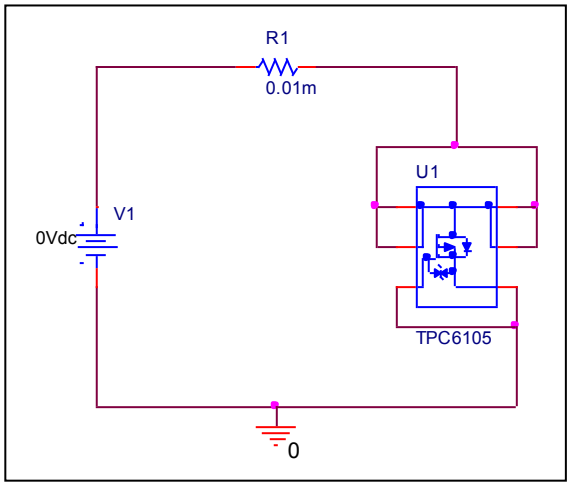


Forward Current Characteristic

Circuit Simulation Result

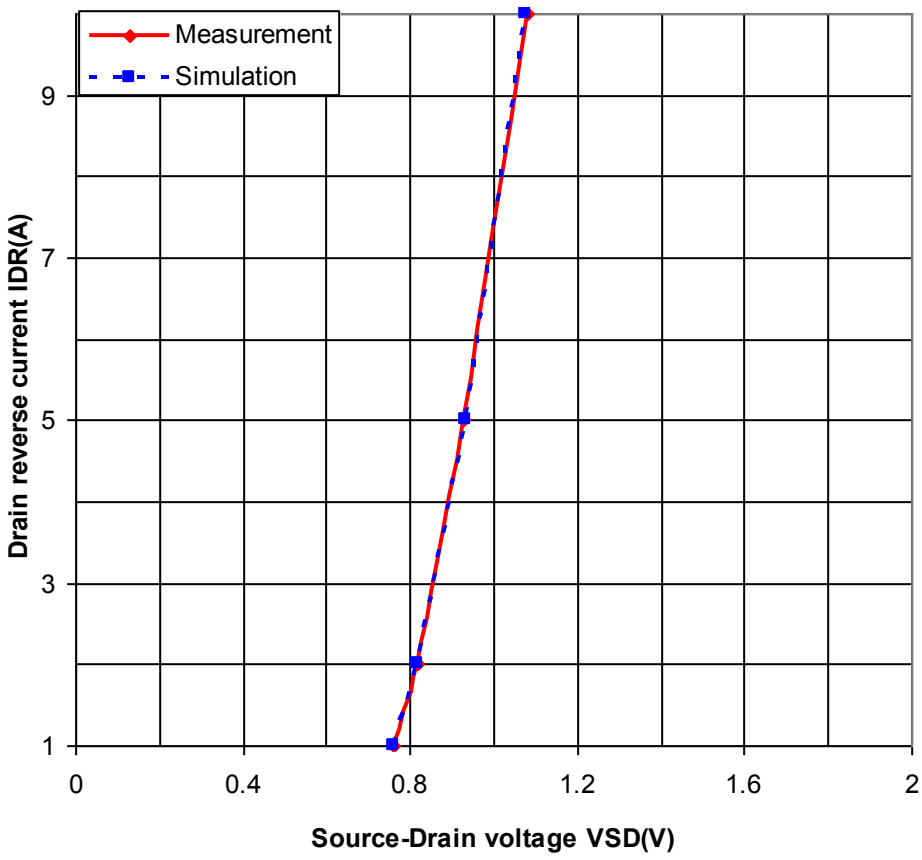


Evaluation Circuit



Comparison Graph

Circuit Simulation Result

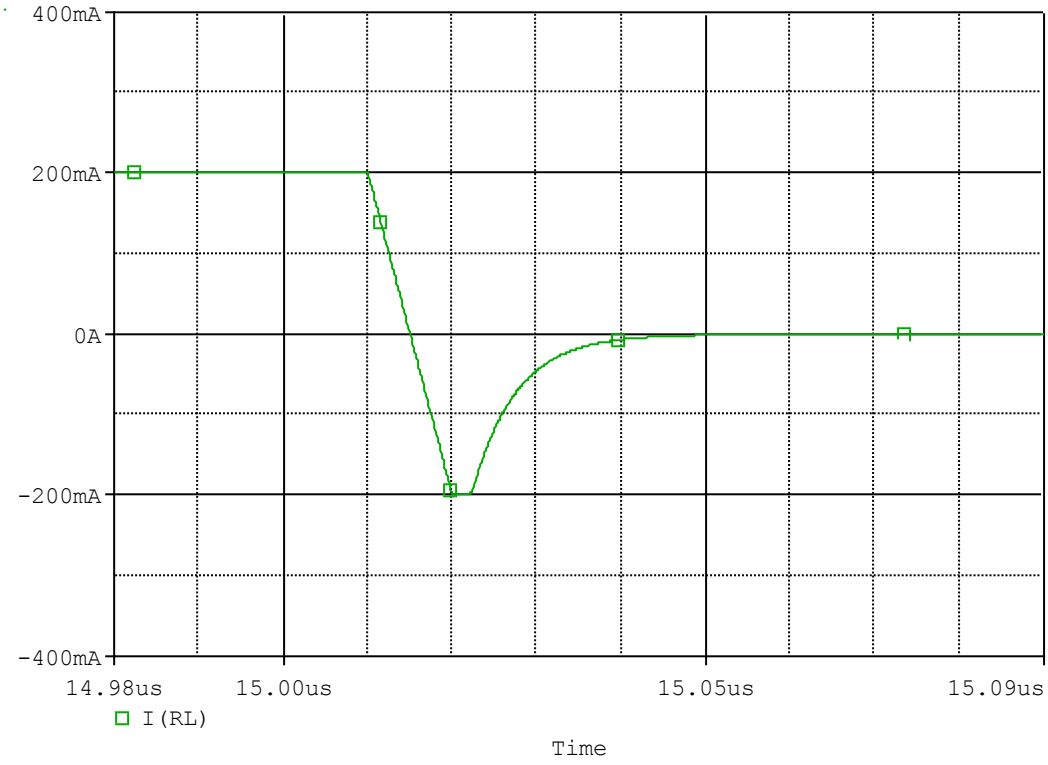


Simulation Result

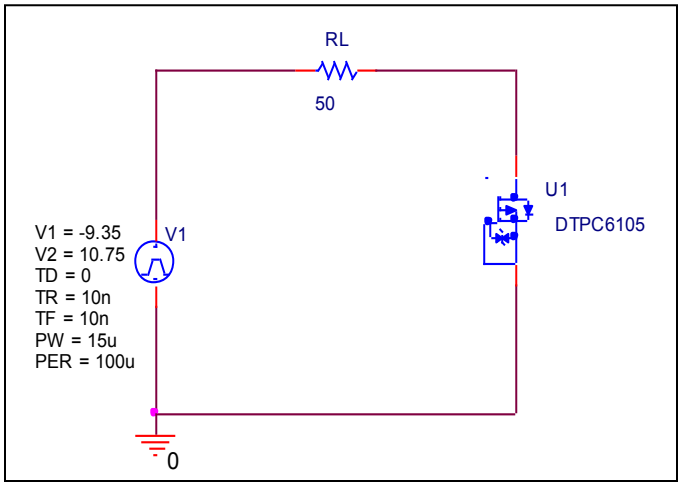
IDR(A)	VSD(V)		%Error
	Measuremen	Simulation	
1	0.76	0.762	0.263
2	0.82	0.817	-0.366
5	0.93	0.931	0.108
10	1.08	1.0754	-0.426

Reverse Recovery Characteristic

Circuit Simulation Result



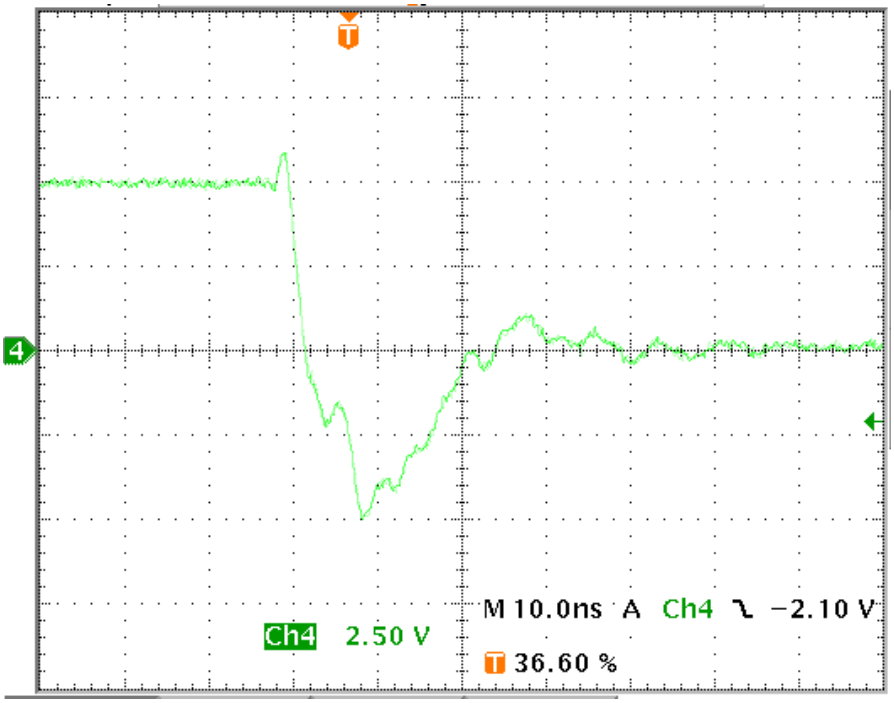
Evaluation Circuit



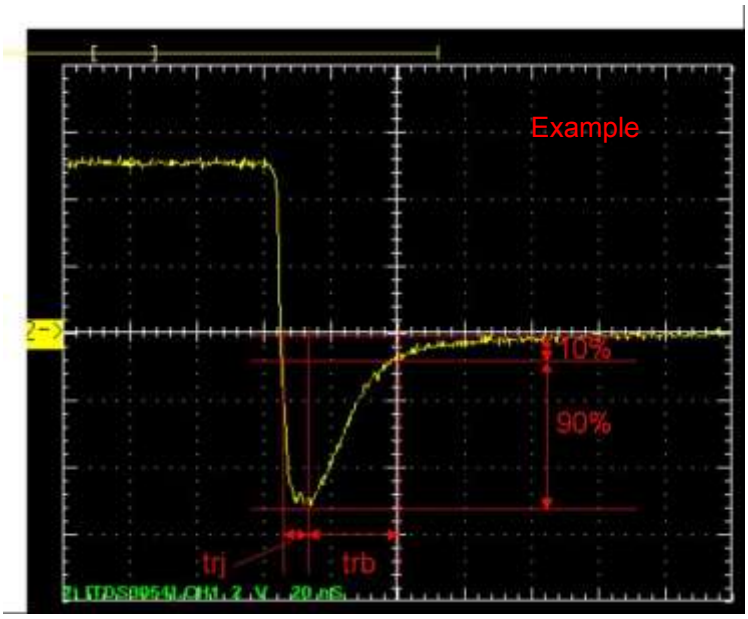
Compare Measurement vs. Simulation

	Measurement	Simulation	Error (%)
Trj(ns)	6.8	6.801	0.015
Trb(ns)	11.8	11.9	0.847
Trr(ns)	18.6	18.701	0.543

Reverse Recovery Characteristic Reference



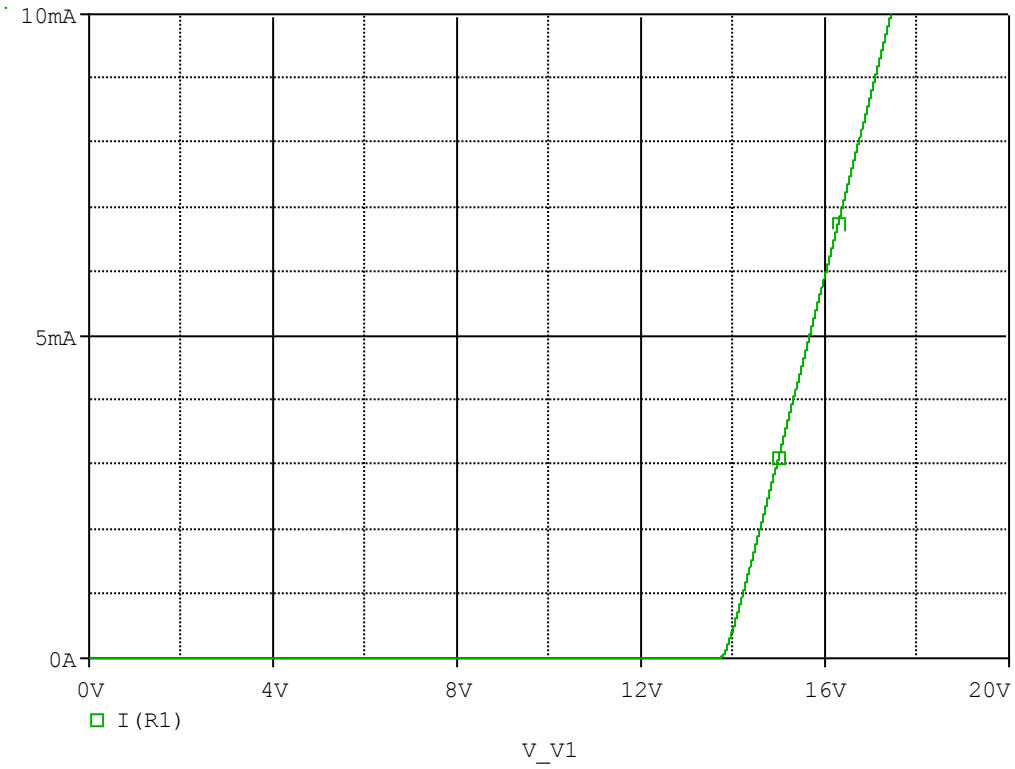
Trj=6.8(ns)
Trb=11.8(ns)
Conditions:Ifwd=Irev=0.2(A),Rl=50



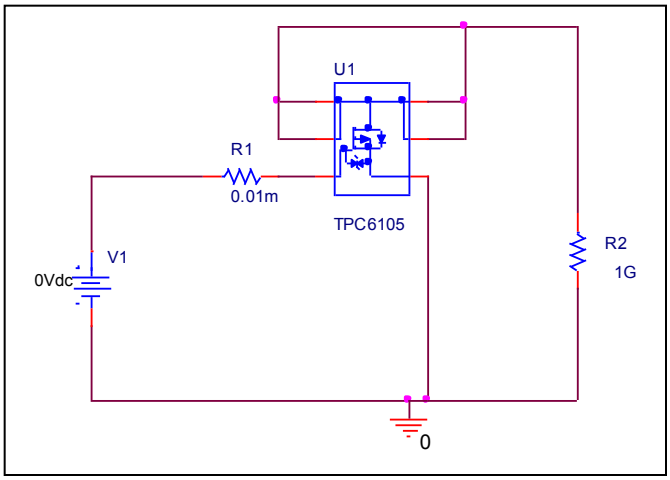
Relation between trj and trb

Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



Zener Voltage Characteristic Reference